

KT9116A

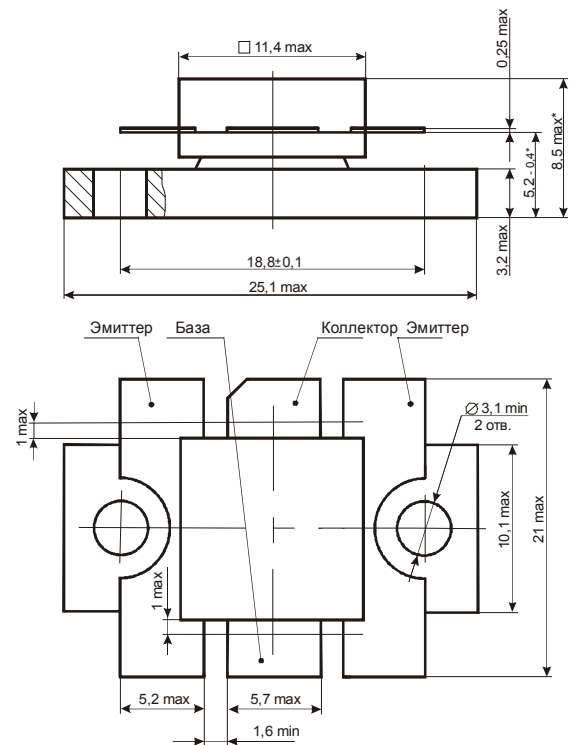
NPN SILICON RF POWER TRANSISTOR

Designed for operation in ultra - linear
Class A low and medium-power amplifiers
of TV transmitters (Band I – III)

- Output power = 5 W (PEP), $f = 225$ MHz, $V_{CC} = 28$ V
- Power gain = 14 dB (min)
- 3 Tone IMD = -58 dB (max)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	55	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	4	A
Operating Junction Temperature	T_j	+200	°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Thermal Resistance (junction to case)	$R_{\theta JC}$	2.5	°C/W
Total Power Dissipation, $T_C = 25$ °C	P_D	70	W



Case KT-56

FUNCTIONAL TESTS

Characteristics	Symbol	Value			Unit
		min	typ	max	
Common-Emitter Amplifier Power Gain ($V_{CC} = 28$ V, $P_{out} = 5$ W PEP, $f = 225$ MHz)	G_P	14			dB
Intermodulation Distortion ⁽²⁾ ($V_{CC} = 28$ V, $P_{out} = 5$ W PEP, $f = 225$ MHz)	3 Tone IMD			-58	dB

NOTE: Three-tone test method (vision carrier: -8dB, sound carrier: -7dB, sideband carrier: -16dB)

ZAO 'SynteZ Microelectronics'

119V Leninsky Prospekt, Voronezh 394007, Russia • Tel +7-4732-379-101 Fax +7-4732-266-057

exim@syntezmicro.ru

www.syntezmicro.ru

Specification is subject to change without notice